

ELECTRON-INDUCED CHANGES
OF OPTICO-REFRACTOMETRIC PARAMETERS
OF GLASSY ALLOYS OF THE $\text{Sb}_2\text{S}_3\text{-GeS}_2$ SYSTEM

M.M. Pop, M.O. Malets, I.I. Shpak, D.G. Semak

Uzhgorod National University,
Research Institute of Solid State Physics and Chemistry
(46, Pidhirna Str., Uzhgorod 88000, Ukraine;
e-mail: *shpak@univ.uzhgorod.ua*)

S u m m a r y

The effect of electron irradiation on the change of optico-refractometric parameters of chalcogenide glassy alloys of the Ge-Sb-S system in the $\text{Sb}_2\text{S}_3\text{-GeS}_2$ section is studied. The composition dependences of the electron-induced effects in the investigated system are analyzed. The obtained results are interpreted in the framework of the model of “switching” of homogeneous and heterogeneous chemical bonds of the matrix of chalcogenide glassy semiconductors.